

AM3962N-VB Datasheet

Dual N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^a | Q_g (Typ.) |
|--------------|---------------------------|------------------------|--------------|
| 60 | 0.048 at $V_{GS} = 10$ V | 4.2 | 4.9 |
| | 0.060 at $V_{GS} = 4.5$ V | 3.6 | |

FEATURES

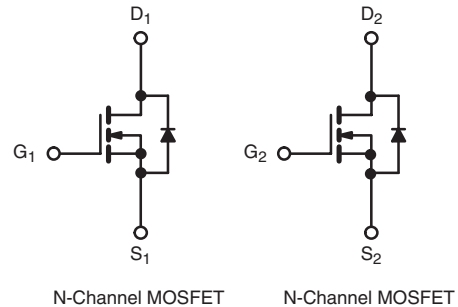
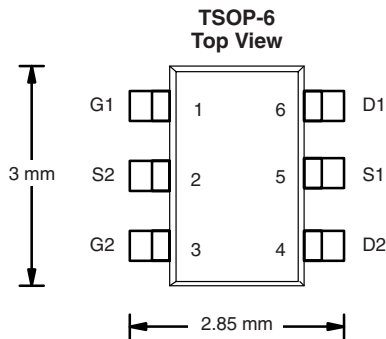
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- CCFL Inverter
- DC/DC Converter
- HDD



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|---------------|------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | A |
| | | $T_C = 70$ °C | |
| | | $T_A = 25$ °C | |
| | | $T_A = 70$ °C | |
| Pulsed Drain Current (10 μ s Pulse Width) | I_{DM} | 16 | |
| Source-Drain Current Diode Current | I_S | $T_C = 25$ °C | |
| | | $T_A = 25$ °C | |
| Pulsed Source-Drain Current | I_{SM} | 16 | |
| Single Pulse Avalanche Current | I_{AS} | 10 | |
| Single Pulse Avalanche Energy | E_{AS} | 5 | |
| Maximum Power Dissipation | P_D | $T_C = 25$ °C | W |
| | | $T_C = 70$ °C | |
| | | $T_A = 25$ °C | |
| | | $T_A = 70$ °C | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | | Symbol | Typ. | Max. | Unit |
|---|---------------|------------|------|------|------|
| Maximum Junction-to-Ambient ^{b, d} | $t \leq 10$ s | R_{thJA} | 49 | 62.5 | °C/W |
| Maximum Junction-to-Foot (Drain) | Steady-State | R_{thJF} | 30 | 40 | |

Notes:

- a. Based on $T_C = 25$ °C.
 b. Surface mounted on 1" x 1" FR4 board.
 c. $t = 10$ s.
 d. Maximum under steady state conditions is 120 °C/W.

| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|--------------------------------------|--|------|-------------------|------|-------|
| Parameter | Symbol | Test Conditions | Min. | Typ. ^a | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 60 | | | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | | 49 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | | | - 5.2 | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 1.2 | | 2.5 | V |
| Gate-Body Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | | | 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | | | 1 | μA |
| | | V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55 °C | | | 10 | |
| On-State Drain Current ^b | I _{D(on)} | V _{DS} = 5 V, V _{GS} = 10 V | 20 | | | A |
| Drain-Source On-State Resistance ^b | R _{DS(on)} | V _{GS} = 10 V, I _D = 4.0A | | 0.048 | | Ω |
| | | V _{GS} = 4.5 V, I _D = 3.0A | | 0.060 | | |
| Forward Transconductance ^b | g _{fs} | V _{DS} = 15 V, I _D = 4.0A | | 35 | | S |
| Dynamic ^a | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 30 V, V _{GS} = 0 V, I _D = 1 MHz | | 580 | | pF |
| Output Capacitance | C _{oss} | | | 100 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 42 | | |
| Total Gate Charge | Q _g | V _{DS} = 30 V, V _{GS} = 10 V, I _D = 4.0 A | | 10 | 15 | nC |
| | | V _{DS} = 30 V, V _{GS} = 4.5 V, I _D = 4.0 A | | 4.9 | 7.4 | |
| Gate-Source Charge | Q _{gs} | | | 1.5 | | |
| Gate-Drain Charge | Q _{gd} | | | 1.5 | | |
| Gate Resistance | R _g | f = 1 MHz | 0.6 | 2.7 | 5.4 | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 30 V, R _L = 2 Ω I _D ≅ 4.0 A, V _{GEN} = 10 V, R _g = 1 Ω | | 7 | 14 | ns |
| Rise Time | t _r | | | 9 | 18 | |
| Turn-Off Delay Time | t _{d(off)} | | | 16 | 32 | |
| Fall Time | t _f | | | 8 | 16 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 20 V, R _L = 2 Ω I _D ≅ 7.0 A, V _{GEN} = 4.5 V, R _g = 1 Ω | | 12 | 24 | |
| Rise Time | t _r | | | 10 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | | | 13 | 26 | |
| Fall Time | t _f | | | 8 | 16 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 2.6 | A |
| Pulse Diode Forward Current ^a | I _{SM} | | | | 50 | |
| Body Diode Voltage | V _{SD} | I _S = 3 A | | 0.77 | 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 5 A, dI/dt = 100 A/μs, T _J = 25 °C | | 15 | 30 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 7.5 | 15 | nC |
| Reverse Recovery Fall Time | t _a | | | 9 | | ns |
| Reverse Recovery Rise Time | t _b | | | 6 | | |

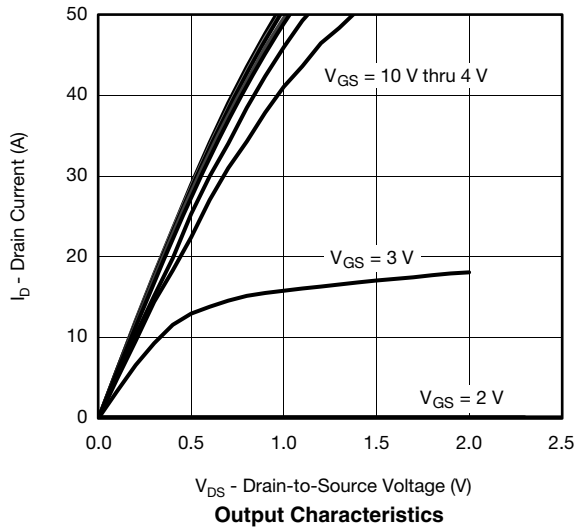
Notes:

a. Guaranteed by design, not subject to production testing.

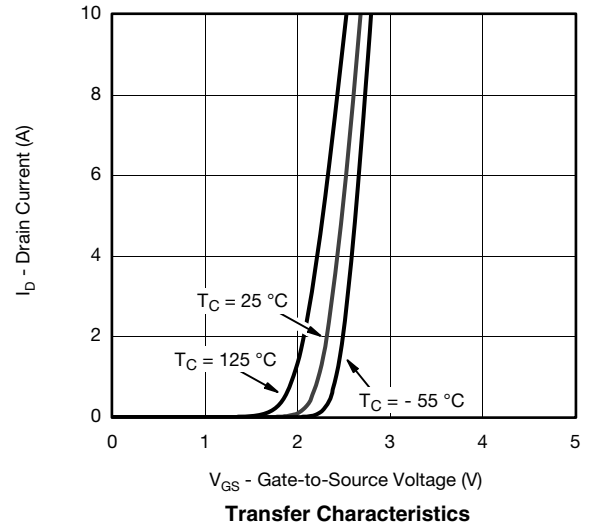
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

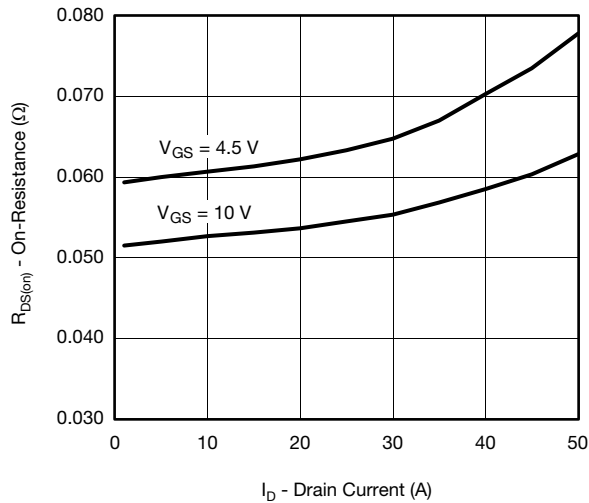
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



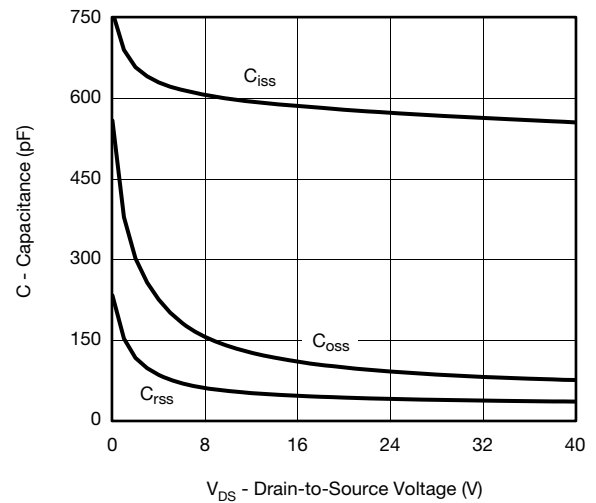
Output Characteristics



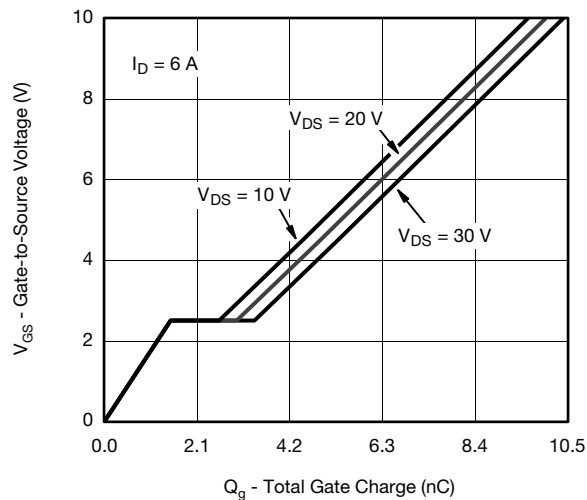
Transfer Characteristics



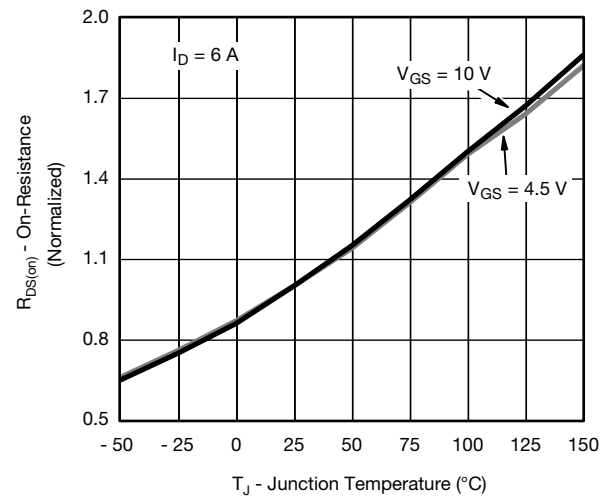
On-Resistance vs. Drain Current



Capacitance

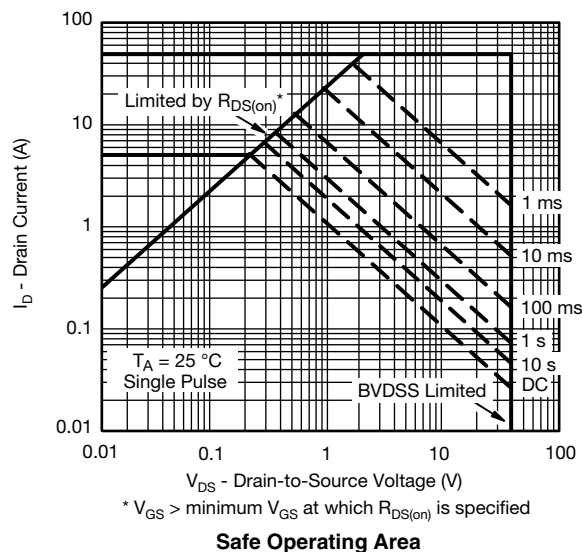
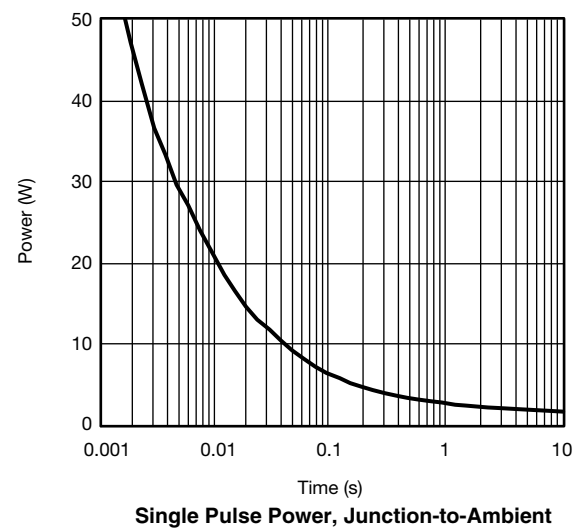
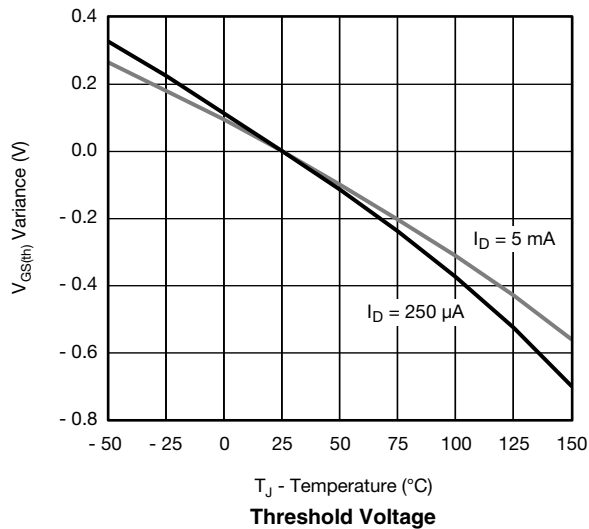
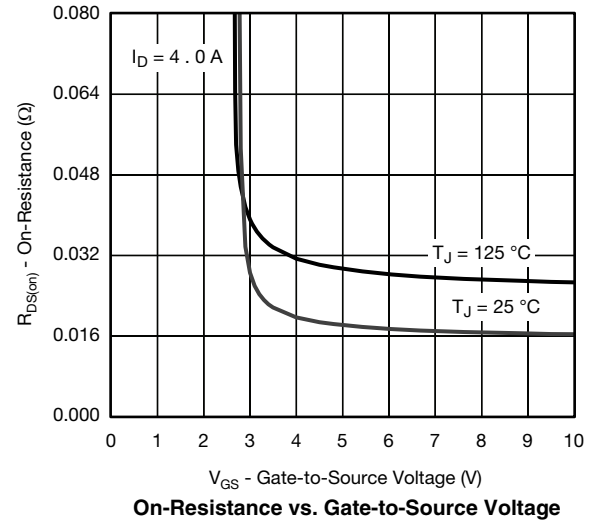
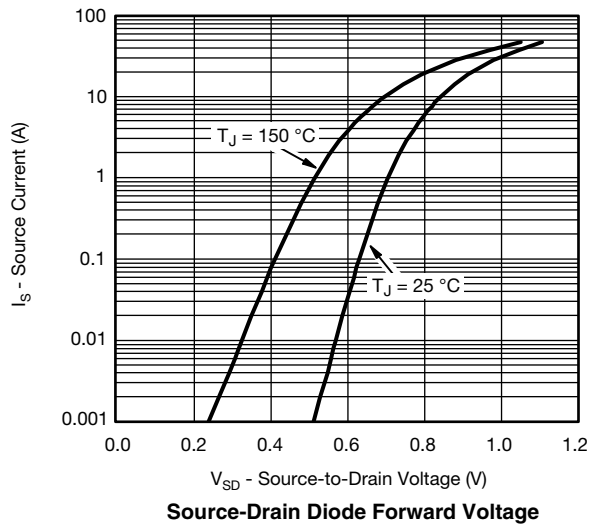


Gate Charge

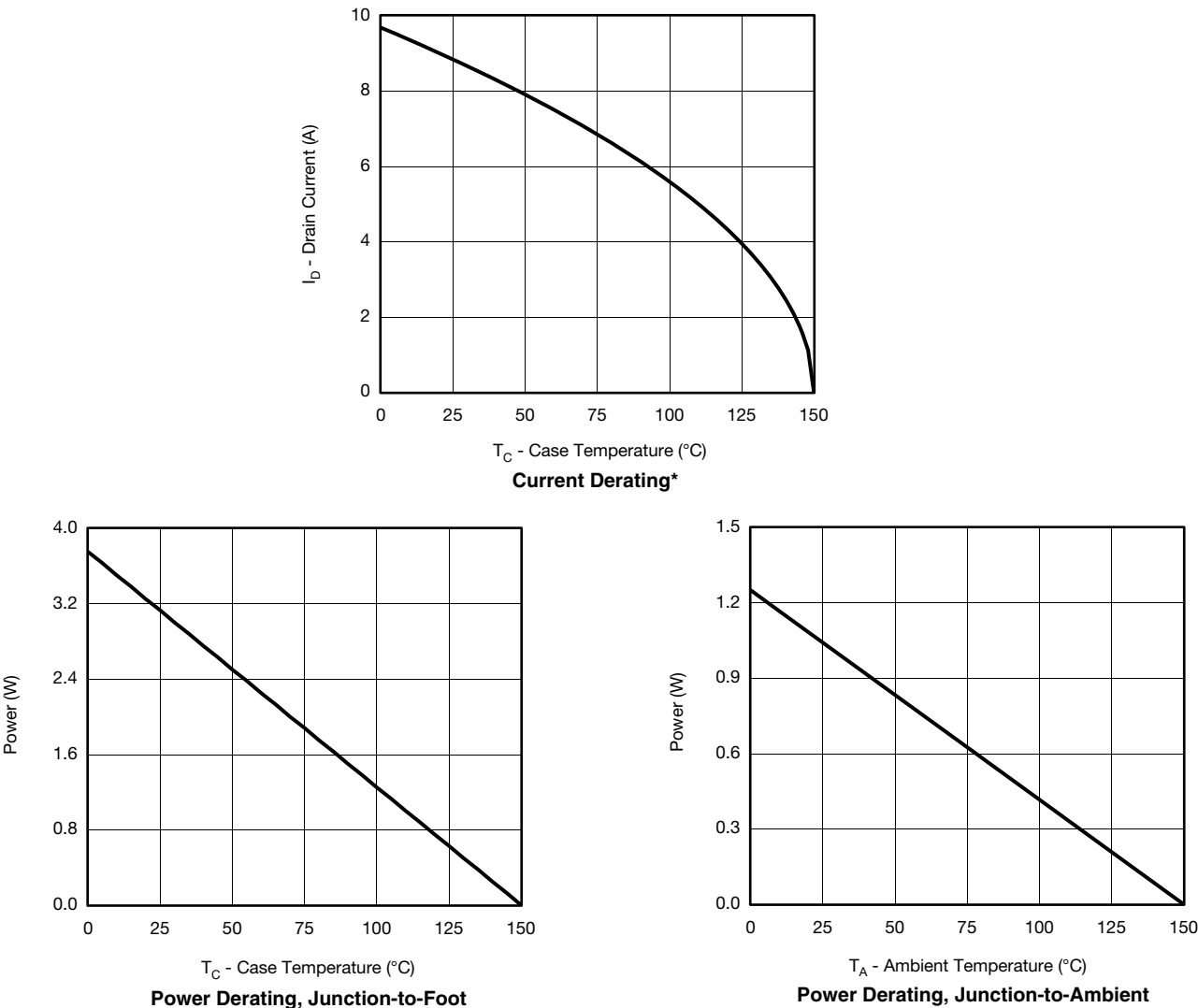


On-Resistance vs. Junction Temperature

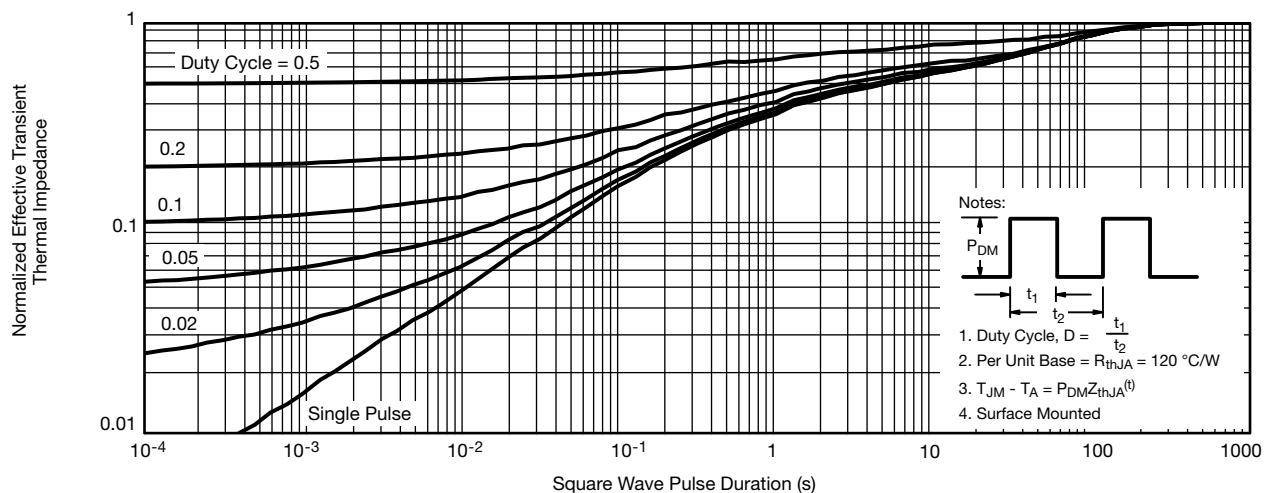
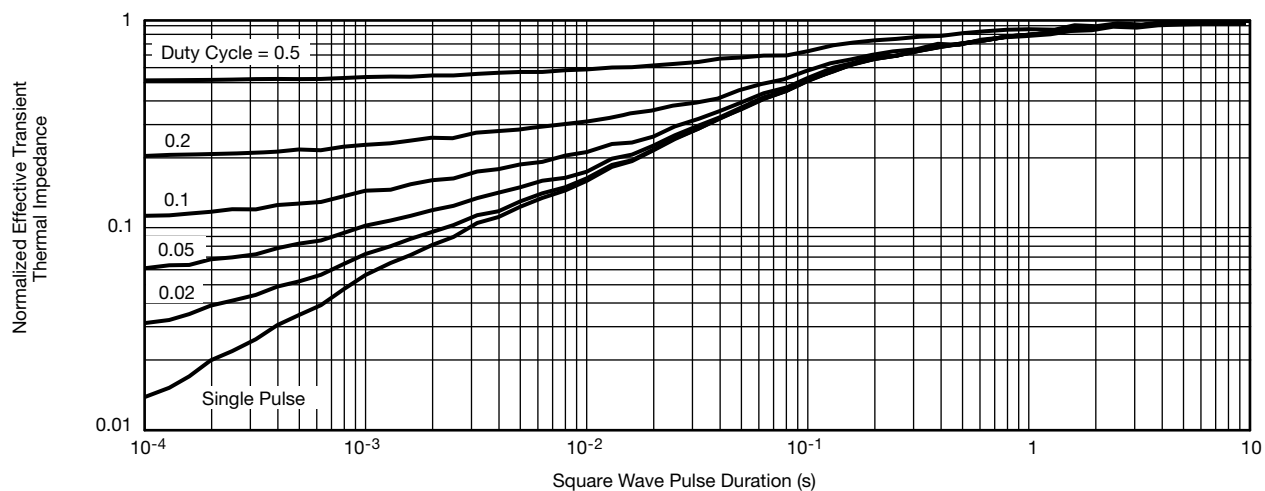
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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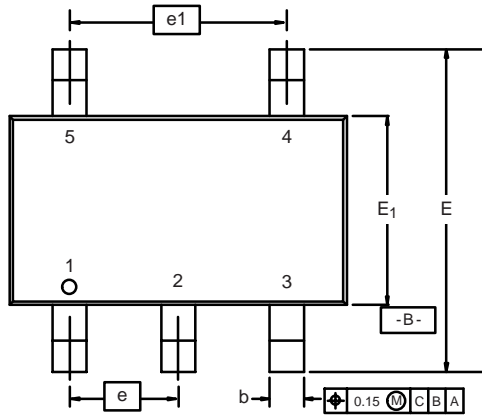


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

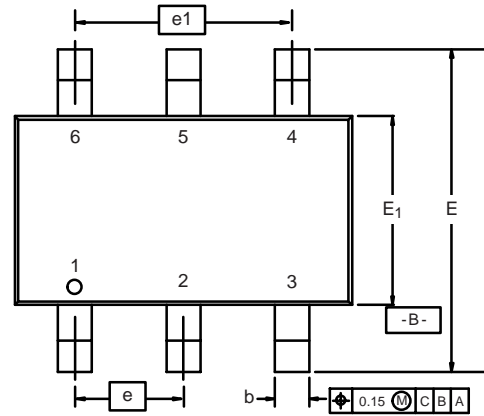
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

TSOP: 5/6-LEAD

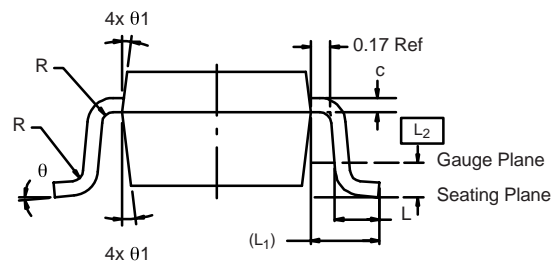
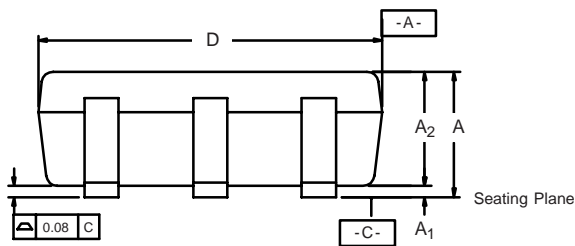
JEDEC Part Number: MO-193C



5-LEAD TSOP

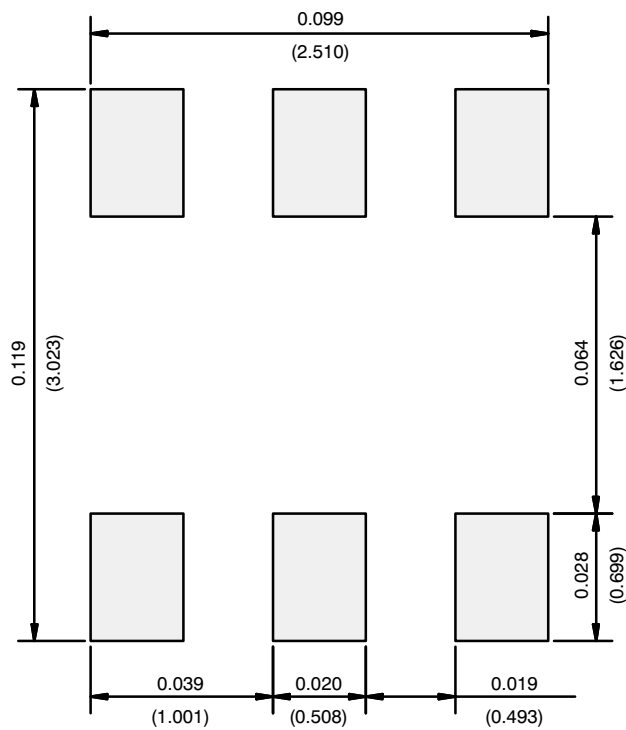


6-LEAD TSOP



| | MILLIMETERS | | | INCHES | | |
|--------------------------------|-------------|------|------|------------|-------|-------|
| Dim | Min | Nom | Max | Min | Nom | Max |
| A | 0.91 | - | 1.10 | 0.036 | - | 0.043 |
| A ₁ | 0.01 | - | 0.10 | 0.0004 | - | 0.004 |
| A ₂ | 0.90 | - | 1.00 | 0.035 | 0.038 | 0.039 |
| b | 0.30 | 0.32 | 0.45 | 0.012 | 0.013 | 0.018 |
| c | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| D | 2.95 | 3.05 | 3.10 | 0.116 | 0.120 | 0.122 |
| E | 2.70 | 2.85 | 2.98 | 0.106 | 0.112 | 0.117 |
| E ₁ | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 |
| e | 0.95 BSC | | | 0.0374 BSC | | |
| e ₁ | 1.80 | 1.90 | 2.00 | 0.071 | 0.075 | 0.079 |
| L | 0.32 | - | 0.50 | 0.012 | - | 0.020 |
| L ₁ | 0.60 Ref | | | 0.024 Ref | | |
| L ₂ | 0.25 BSC | | | 0.010 BSC | | |
| R | 0.10 | - | - | 0.004 | - | - |
| θ | 0° | 4° | 8° | 0° | 4° | 8° |
| θ ₁ | 7° Nom | | | 7° Nom | | |
| ECN: C-06593-Rev. I, 18-Dec-06 | | | | | | |
| DWG: 5540 | | | | | | |

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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